Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 245724US2X	SERIAL NO. 10/717,718 ~~New Application~~
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Yasutaka NISHIOKA, et al.	
		FILING DATE ~~Herewith~~	GROUP 3729

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	TRANSLATION NO
CJG	AO	2000-269326	9/29/00	Japan (with English Extract)		X
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

CJG	AW	S. M. JANG, et al., "INTEGRATION OF CU AND LOW-K MATERIAL FOR DUAL-DAMASCENE PROCESS", Semiconductor Technology, (ISTC 2001), Vol. I, Pages 485-493
CJG	AX	K. HIGASHI, et al., "A MANUFACTURABLE COPPER/LOW-K SiOC/SiCN PROCESS TECHNOLOGY FOR 90NM-NODE HIGH PERFORMANCE eDRAM", Proceedings of the 2002 International Interconnect Technology Conference, Pages 15-17
CJG	AY	M. FAYOLLE, et al., "INTEGRATION OF Cu/SiOC IN DUAL DAMASCENE INTERCONNECT FOR 0.1μm TECHNOLOGY USING A NEW SiC MATERIAL AS DIELECTRIC BARRIER", Proceedings of the 2002 International Interconnect Technology Conference, Pages 39-41
	AZ	☐ Additional References sheet(s) attached

Examiner	Carl J. Arbes	Date Considered	3/4/05

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.